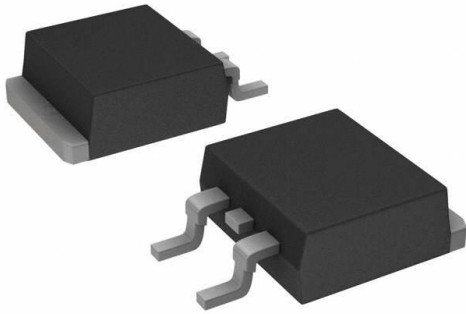


NTD60N02RG Datasheet

www.digi-electronics.com



DiGi Electronics Part Number	NTD60N02RG-DG
Manufacturer	onsemi
Manufacturer Product Number	NTD60N02RG
Description	MOSFET N-CH 25V 8.5A/32A DPAK
Detailed Description	N-Channel 25 V 8.5A (Ta), 32A (Tc) 1.25W (Ta), 58W (Tc) Surface Mount DPAK

<https://www.DiGi-Electronics.com>



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

NTD60N02RG

Series:

-

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

25 V

Drive Voltage (Max Rds On, Min Rds On):

4.5V, 10V

Vgs(th) (Max) @ Id:

2V @ 250µA

Vgs (Max):

±20V

FET Feature:

-

Operating Temperature:

-55°C ~ 175°C (Tj)

Supplier Device Package:

DPAK

Base Product Number:

NTD60

Manufacturer:

onsemi

Product Status:

Obsolete

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

8.5A (Ta), 32A (Tc)

Rds On (Max) @ Id, Vgs:

10.5mOhm @ 20A, 10V

Gate Charge (Qg) (Max) @ Vgs:

14 nC @ 4.5 V

Input Capacitance (Ciss) (Max) @ Vds:

1330 pF @ 20 V

Power Dissipation (Max):

1.25W (Ta), 58W (Tc)

Mounting Type:

Surface Mount

Package / Case:

TO-252-3, DPAK (2 Leads + Tab), SC-63

Environmental & Export classification

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

ON Semiconductor

Is Now

The logo for onsemi, featuring the word "onsemi" in a dark teal, lowercase, sans-serif font. The letter "i" is stylized with a white dot and a teal vertical bar. A small orange triangle is positioned above the top right of the "i". A trademark symbol (TM) is located to the right of the logo.

To learn more about onsemi™, please visit our website at
www.onsemi.com

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NTD60N02R

Power MOSFET

62 A, 25 V, N-Channel, DPAK



ON Semiconductor®

<http://onsemi.com>

Features

- Planar HD3e Process for Fast Switching Performance
- Low $R_{DS(on)}$ to Minimize Conduction Loss
- Low C_{iss} to Minimize Driver Loss
- Low Gate Charge
- Optimized for High Side Switching Requirements in High-Efficiency DC-DC Converters
- Pb-Free Packages are Available

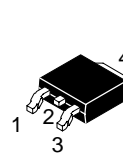
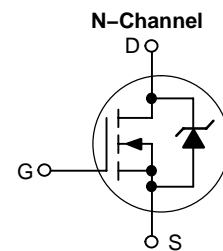
MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	25	Vdc
Gate-to-Source Voltage – Continuous	V_{GS}	± 20	Vdc
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	2.6	$^\circ\text{C/W}$
Total Power Dissipation @ $T_C = 25^\circ\text{C}$	P_D	58	W
Drain Current	I_D	62	A
Continuous @ $T_C = 25^\circ\text{C}$, Chip	I_D	62	A
Continuous @ $T_C = 25^\circ\text{C}$, Limited by Package	I_D	50	A
Continuous @ $T_A = 25^\circ\text{C}$, Limited by Wires	I_D	32	A
Thermal Resistance Junction-to-Ambient (Note 1)	$R_{\theta JA}$	80	$^\circ\text{C/W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	P_D	1.87	W
Drain Current – Continuous @ $T_A = 25^\circ\text{C}$	I_D	10.5	A
Thermal Resistance Junction-to-Ambient (Note 2)	$R_{\theta JA}$	120	$^\circ\text{C/W}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	P_D	1.25	W
Drain Current – Continuous @ $T_A = 25^\circ\text{C}$	I_D	8.5	A
Operating and Storage Temperature	T_J , and T_{stg}	-55 to 175	$^\circ\text{C}$
Single Pulse Drain-to-Source Avalanche Energy – Starting $T_J = 25^\circ\text{C}$ ($V_{DD} = 50$ Vdc, $V_{GS} = 10.0$ Vdc, $I_L = 11$ Apk, $L = 1.0$ mH, $R_G = 25$ Ω)	E_{AS}	60	mJ
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T_L	260	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. When surface mounted to an FR4 board using 0.5 in sq drain pad size.
2. When surface mounted to an FR4 board using the minimum recommended pad size.

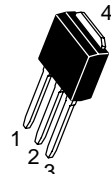
$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D MAX
25 V	8.4 m Ω @ 10 V	62 A



CASE 369AA
DPAK
(Surface Mount)
STYLE 2

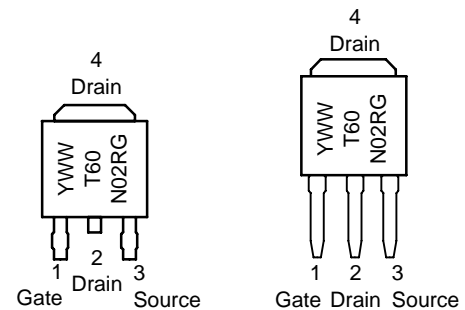


CASE 369AC
3 IPAK



CASE 369D
DPAK
(Straight Lead)
STYLE 2

MARKING DIAGRAM & PIN ASSIGNMENTS



Y = Year
WW = Work Week
T60N02R = Device Code
G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

NTD60N02R**ELECTRICAL CHARACTERISTICS** ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain-to-Source Breakdown Voltage (Note 3) ($V_{GS} = 0\text{ Vdc}$, $I_D = 250\ \mu\text{Adc}$) Temperature Coefficient (Positive)	$V_{(BR)DSS}$	25 –	27.5 25.5	– –	Vdc mV/ $^\circ\text{C}$
Zero Gate Voltage Drain Current ($V_{DS} = 20\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$) ($V_{DS} = 20\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$, $T_J = 150^\circ\text{C}$)	I_{DSS}	– –	– –	1.5 10	μAdc
Gate-Body Leakage Current ($V_{GS} = \pm 20\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	–	–	± 100	nAdc

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage (Note 3) ($V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{Adc}$) Threshold Temperature Coefficient (Negative)	$V_{GS(th)}$	1.0 –	1.5 4.1	2.0 –	Vdc mV/ $^\circ\text{C}$
Static Drain-to-Source On-Resistance (Note 3) ($V_{GS} = 4.5\text{ Vdc}$, $I_D = 15\text{ Adc}$) ($V_{GS} = 10\text{ Vdc}$, $I_D = 20\text{ Adc}$) ($V_{GS} = 10\text{ Vdc}$, $I_D = 31\text{ Adc}$)	$R_{DS(on)}$	– – –	11.2 8.4 8.2	12.5 10.5 –	m Ω
Forward Transconductance ($V_{DS} = 10\text{ Vdc}$, $I_D = 15\text{ Adc}$) (Note 3)	g_{FS}	–	27	–	Mhos

DYNAMIC CHARACTERISTICS

Input Capacitance	$(V_{DS} = 20\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$, $f = 1.0\text{ MHz}$)	C_{iss}	–	1000	1330	pF
Output Capacitance		C_{oss}	–	480	640	
Transfer Capacitance		C_{rss}	–	180	225	

SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	$(V_{GS} = 10\text{ Vdc}$, $V_{DD} = 10\text{ Vdc}$, $I_D = 31\text{ Adc}$, $R_G = 3.0\ \Omega$)	$t_{d(on)}$	–	7.0	–	ns
Rise Time		t_r	–	33	–	
Turn-Off Delay Time		$t_{d(off)}$	–	19	–	
Fall Time		t_f	–	9.0	–	
Gate Charge	$(V_{GS} = 4.5\text{ Vdc}$, $I_D = 31\text{ Adc}$, $V_{DS} = 10\text{ Vdc}$) (Note 3)	Q_T	–	9.5	14	nC
		Q_{GS}	–	2.2	–	
		Q_{GD}	–	5.0	–	

SOURCE-DRAIN DIODE CHARACTERISTICS

Forward On-Voltage	$(I_S = 20\text{ Adc}$, $V_{GS} = 0\text{ Vdc}$) (Note 3) $(I_S = 31\text{ Adc}$, $V_{GS} = 0\text{ Vdc}$) $(I_S = 15\text{ Adc}$, $V_{GS} = 0\text{ Vdc}$, $T_J = 125^\circ\text{C}$)	V_{SD}	– – –	0.88 1.15 0.80	1.2 – –	Vdc
Reverse Recovery Time	$(I_S = 31\text{ Adc}$, $V_{GS} = 0\text{ Vdc}$, $di_S/dt = 100\text{ A}/\mu\text{s}$) (Note 3)	t_{rr}	–	29.1	–	ns
		t_a	–	13.6	–	
		t_b	–	15.5	–	
Reverse Recovery Stored Charge		Q_{rr}	–	0.02	–	μC

3. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$.

4. Switching characteristics are independent of operating junction temperatures.

NTD60N02R

TYPICAL CHARACTERISTICS

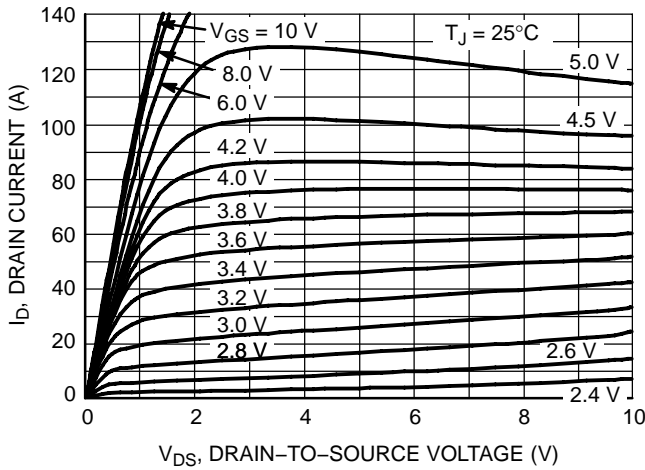


Figure 1. On-Region Characteristics

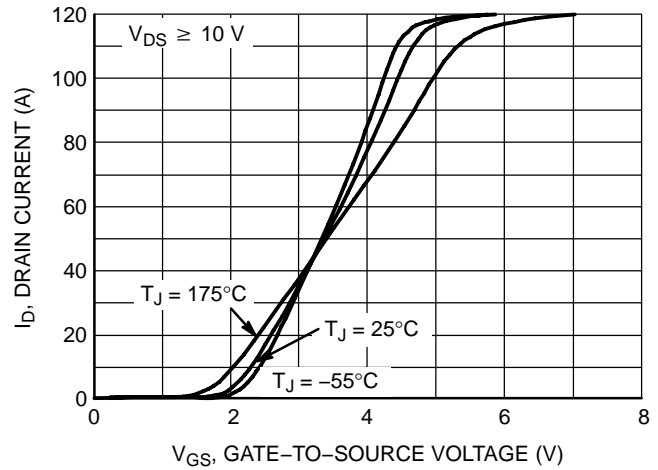


Figure 2. Transfer Characteristics

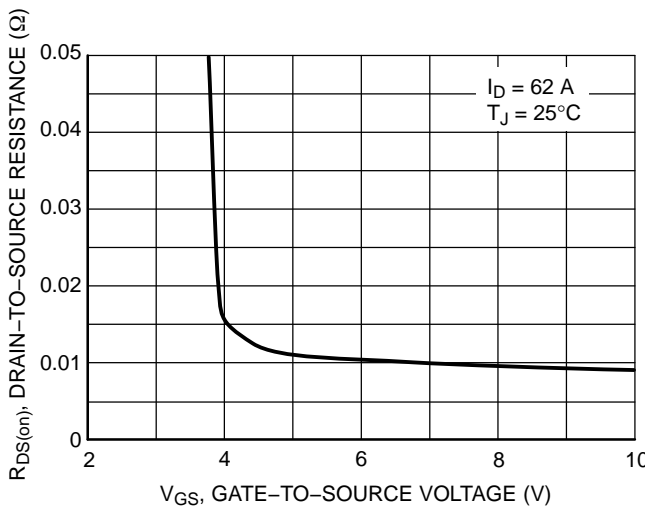


Figure 3. On-Resistance versus Gate-to-Source Voltage

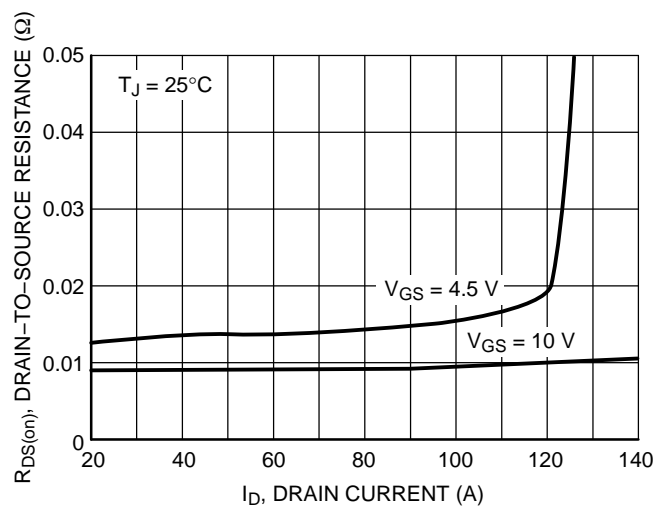


Figure 4. On-Resistance versus Drain Current and Gate Voltage

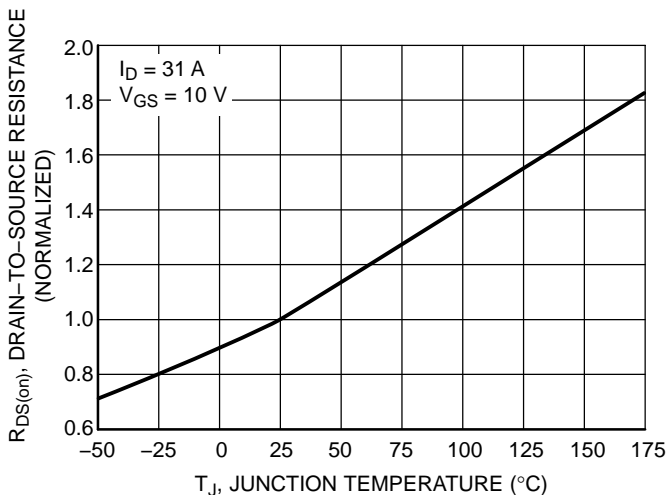


Figure 5. On-Resistance Variation with Temperature

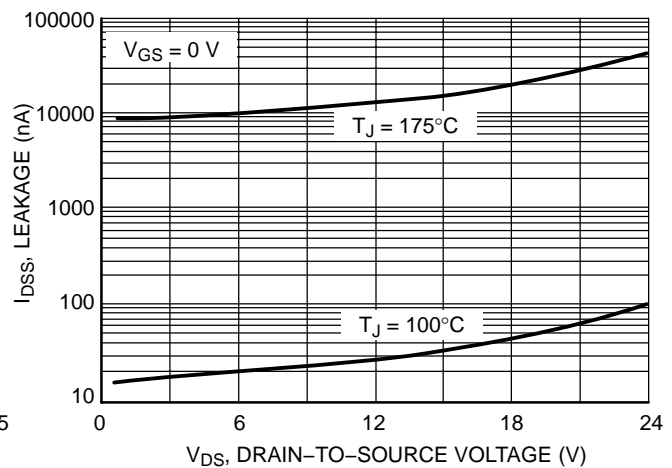


Figure 6. Drain-to-Source Leakage Current versus Voltage

NTD60N02R

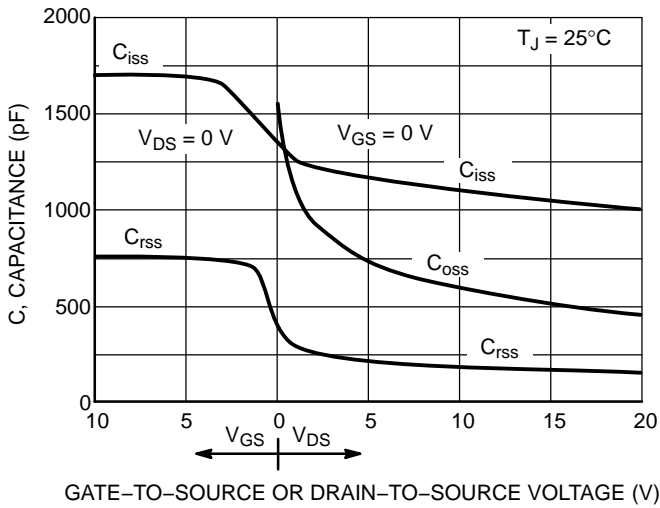


Figure 7. Capacitance Variation

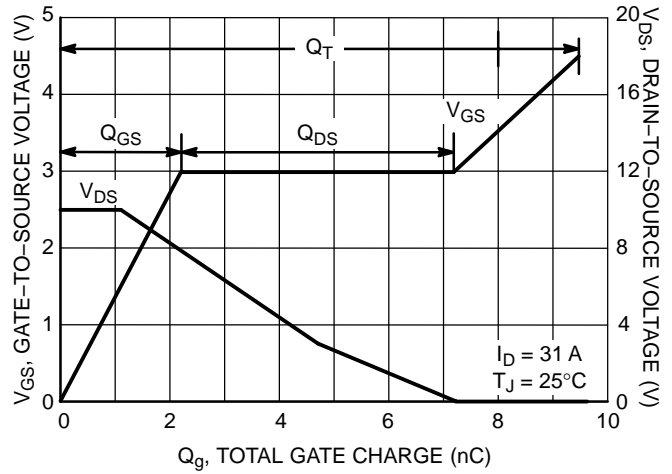


Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Charge

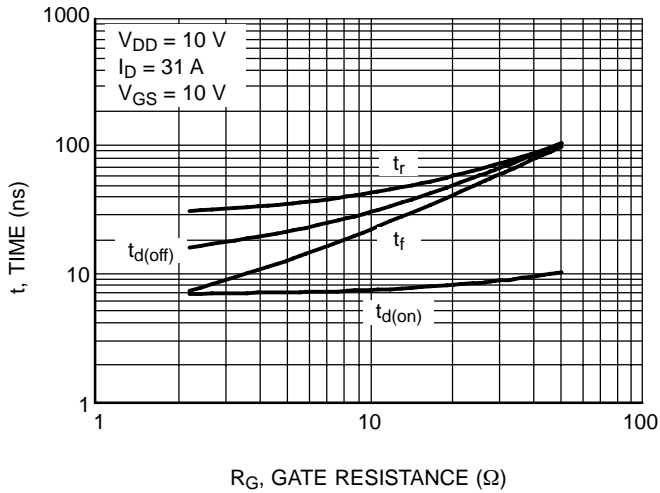


Figure 9. Resistive Switching Time Variation versus Gate Resistance

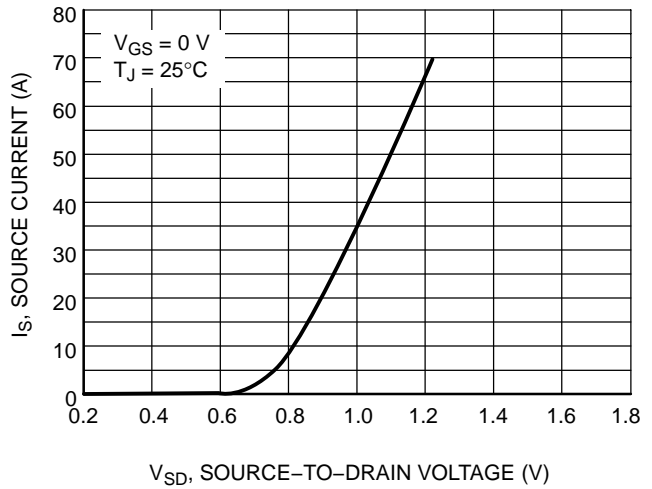


Figure 10. Diode Forward Voltage versus Current

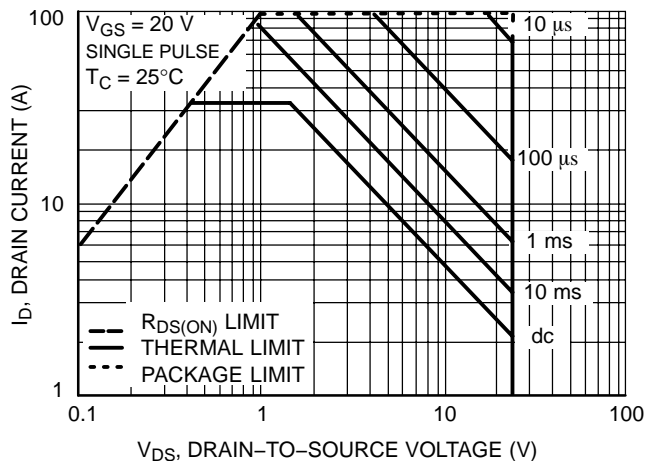


Figure 11. Maximum Rated Forward Biased Safe Operating Area

NTD60N02R

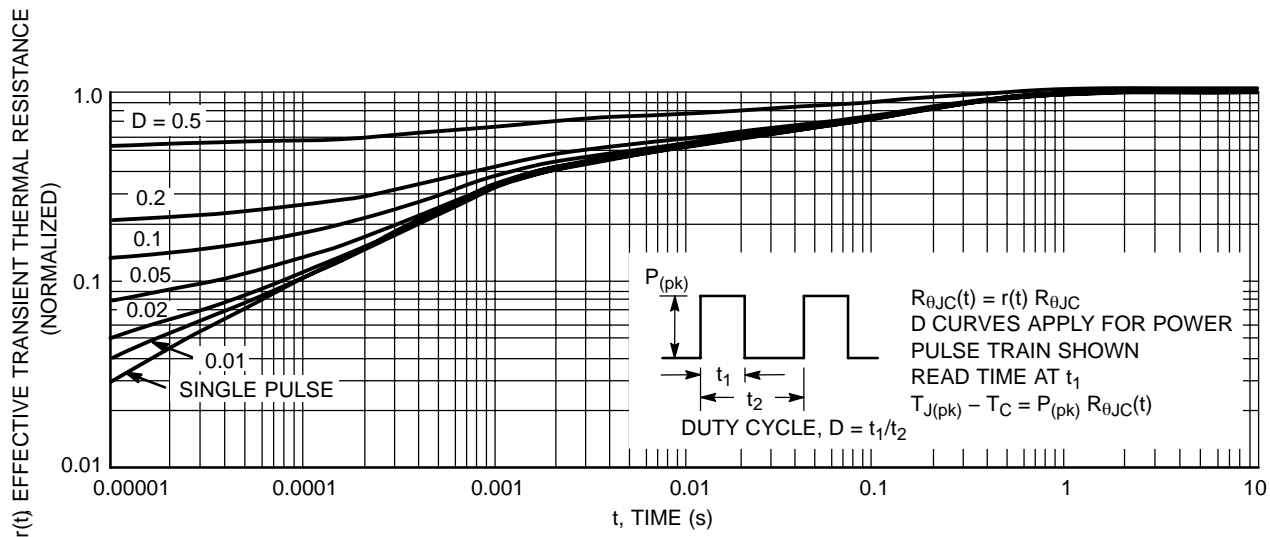


Figure 12. Thermal Response

ORDERING INFORMATION

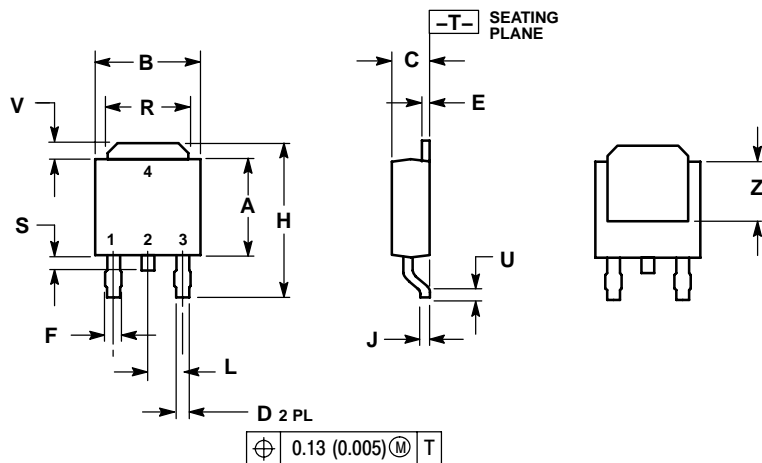
Order Number	Package	Shipping†
NTD60N02R	DPAK-3	75 Units / Rail
NTD60N02RG	DPAK-3 (Pb-Free)	75 Units / Rail
NTD60N02RT4	DPAK-3	2500 / Tape & Reel
NTD60N02RT4G	DPAK-3 (Pb-Free)	2500 / Tape & Reel
NTD60N02R-1	DPAK-3 Straight Lead	75 Units / Rail
NTD60N02R-1G	DPAK-3 Straight Lead (Pb-Free)	75 Units / Rail
NTD60N02R-35	DPAK-3 Straight Lead (3.5 ± 0.15 mm)	75 Units / Rail
NTD60N02R-35G	DPAK-3 Straight Lead (3.5 ± 0.15 mm) (Pb-Free)	75 Units / Rail

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTD60N02R

PACKAGE DIMENSIONS

DPAK
CASE 369AA-01
ISSUE A

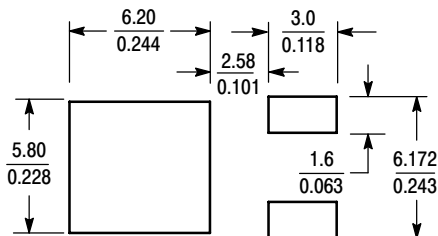


- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.22
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.025	0.035	0.63	0.89
E	0.018	0.024	0.46	0.61
F	0.030	0.045	0.77	1.14
H	0.386	0.410	9.80	10.40
J	0.018	0.023	0.46	0.58
L	0.090 BSC		2.29 BSC	
R	0.180	0.215	4.57	5.45
S	0.024	0.040	0.60	1.01
U	0.020	----	0.51	----
V	0.035	0.050	0.89	1.27
Z	0.155	----	3.93	----

- STYLE 2:
 PIN 1. GATE
 2. DRAIN
 3. SOURCE
 4. DRAIN

SOLDERING FOOTPRINT*



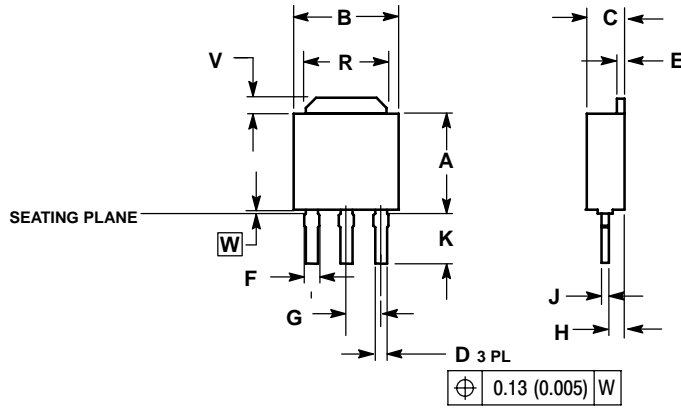
SCALE 3:1 (mm / inches)

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NTD60N02R

PACKAGE DIMENSIONS

3 IPAk, STRAIGHT LEAD CASE 369AC-01 ISSUE O



NOTES:

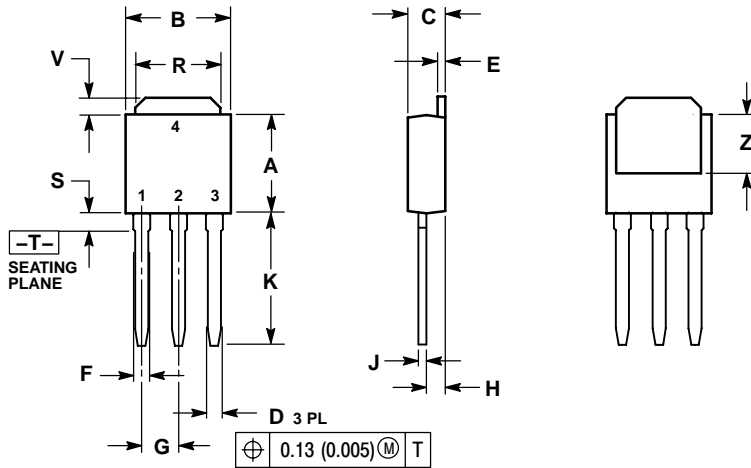
- 1.. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2.. CONTROLLING DIMENSION: INCH.
3. SEATING PLANE IS ON TOP OF DAMBAR POSITION.
4. DIMENSION A DOES NOT INCLUDE DAMBAR POSITION OR MOLD GATE.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.22
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.043	0.94	1.09
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.134	0.142	3.40	3.60
R	0.180	0.215	4.57	5.46
V	0.035	0.050	0.89	1.27
W	0.000	0.010	0.000	0.25

NTD60N02R

PACKAGE DIMENSIONS

DPAK
CASE 369D-01
ISSUE B



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

- STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

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ON Semiconductor Website: www.onsemi.com
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OUR CERTIFICATE

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